# imall

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Preferred Devices

## Dual Common Base-Collector Bias Resistor Transistors

## NPN and PNP Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. The NSTB1005DXV5T1 contains two complementary BRT devices are housed in the SOT-553 package which is ideal for low power surface mount applications where board space is at a premium.

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- Available in 8 mm, 7 inch Tape and Reel
- Lead Free

**MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$  unless otherwise noted, common for  $Q_1$  and  $Q_2$ , – minus sign for  $Q_1$  (PNP) omitted)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	V <sub>CEO</sub>	50	Vdc
Collector Current	Ι <sub>C</sub>	100	mAdc

#### THERMAL CHARACTERISTICS

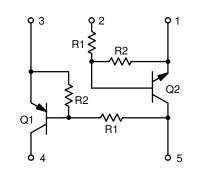
Characteristic (One Junction Heated)	Symbol	Мах	Unit	
Total Device Dissipation T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	357 (Note 1) 2.9 (Note 1)	mW mW/°C	
Thermal Resistance – Junction-to-Ambient	R <sub>θJA</sub>	350 (Note 1)	°C/W	
Characteristic (Both Junctions Heated)	Symbol	Мах	Unit	
Total Device Dissipation T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	500 (Note 1) 4.0 (Note 1)	mW mW/°C	
Thermal Resistance – Junction-to-Ambient	R <sub>θJA</sub>	250 (Note 1)	°C/W	
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	

1. FR-4 @ Minimum Pad



## ON Semiconductor<sup>®</sup>

http://onsemi.com





#### CASE 463B

#### **MARKING DIAGRAM**



UC = Specific Device Code D = Date Code

#### **ORDERING INFORMATION**

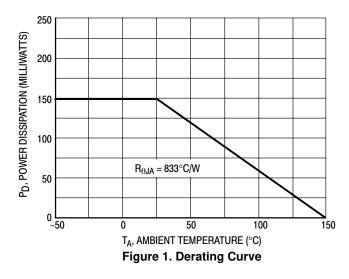
Device	Package	Shipping <sup>†</sup>
NSTB1005DXV5T1	SOT-553	4 mm pitch 4000/Tape & Reel
NSTB1005DXV5T5	SOT-553	2 mm pitch 8000/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

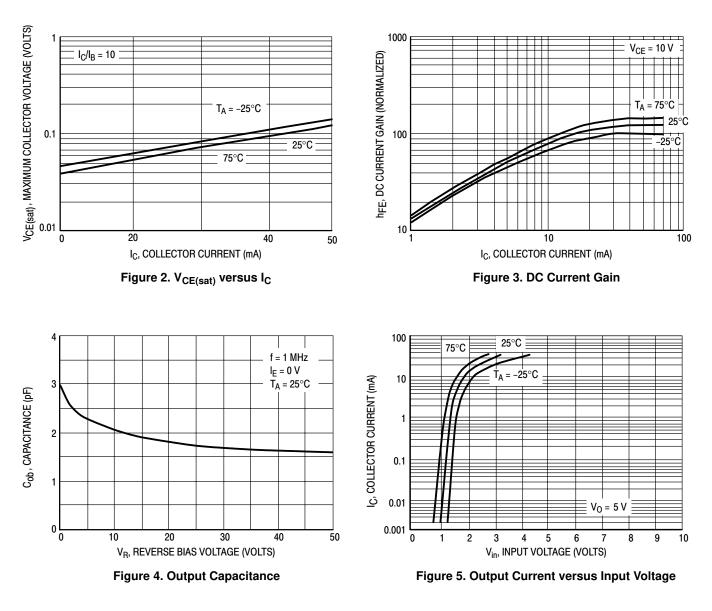
**Preferred** devices are recommended choices for future use and best overall value.

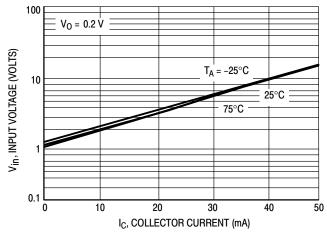
Characteristic	Symbol	Min	Тур	Max	Unit
Q1 TRANSISTOR: PNP – OFF CHARACTERISTICS					
Collector–Base Cutoff Current ( $V_{CB} = 50 \text{ V}, I_E = 0$ )	I <sub>CBO</sub>	-	-	100	nAdc
Collector–Emitter Cutoff Current ( $V_{CE} = 50 \text{ V}, I_B = 0$ )	I <sub>CEO</sub>	-	-	500	nAdc
Emitter-Base Cutoff Current	I <sub>EBO</sub>	-	-	0.1	mAdc
Collector–Base Breakdown Voltage ( $I_C = 10 \ \mu A$ , $I_E = 0$ )	V <sub>(BR)CBO</sub>	50	-	-	Vdc
Collector–Emitter Breakdown Voltage ( $I_C = 2.0 \text{ mA}, I_B = 0$ )	V <sub>(BR)CEO</sub>	50	-	-	Vdc
ON CHARACTERISTICS		•			•
DC Current Gain	h <sub>FE</sub>	80	140	-	
Collector–Emitter Saturation Voltage ( $I_C = 10 \text{ mA}, I_E = 0.3 \text{ mA}$ )	V <sub>CE(sat)</sub>	-	-	0.25	Vdc
Output Voltage (on) (V_{CC} = 5.0 V, V_B = 3.5 V, R_L = 1.0 k $\Omega$ )	V <sub>OL</sub>	-	-	0.2	Vdc
Output Voltage (off) (V_{CC} = 5.0 V, V_B = 0.5 V, RL = 1.0 k $\Omega$ )	V <sub>OH</sub>	4.9	-	-	Vdc
Input Resistor	R1	32.9	47	61.1	kΩ
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	0.8	1.0	1.2	
Q2 TRANSISTOR: NPN – OFF CHARACTERISTICS		•			
Collector-Base Cutoff Current ( $V_{CB} = 50 \text{ V}, I_E = 0$ )	I <sub>CBO</sub>	-	-	100	nAdc
Collector-Emitter Cutoff Current ( $V_{CB} = 50 \text{ V}, I_B = 0$ )	I <sub>CEO</sub>	-	-	500	nAdc
Emitter-Base Cutoff Current $(V_{EB} = 6.0, I_C = 5.0 \text{ mA})$	I <sub>EBO</sub>	-	-	0.1	mAdc
ON CHARACTERISTICS					
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 $\mu$ A, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	50	-	-	Vdc
Collector-Emitter Breakdown Voltage ( $I_C = 2.0 \text{ mA}, I_B = 0$ )	V <sub>(BR)CEO</sub>	50	-	-	Vdc
DC Current Gain $(V_{CE} = 10 \text{ V}, I_C = 5.0 \text{ mA})$	h <sub>FE</sub>	80	140	-	
Collector–Emitter Saturation Voltage ( $I_C = 10 \text{ mA}, I_B = 0.3 \text{ mA}$ )	V <sub>CE(SAT)</sub>	-	-	0.25	Vdc
Output Voltage (on) (V_{CC} = 5.0 V, V_B = 2.5 V, R_L = 1.0 k\Omega)	V <sub>OL</sub>	-	-	0.2	Vdc
Output Voltage (off) (V_{CC} = 5.0 V, V_B = 0.5 V, R_L = 1.0 k\Omega)	V <sub>OH</sub>	4.9	- 1	-	Vdc
Input Resistor	R1	33	47	61	kΩ
Resistor Ratio	R1/R2	0.8	1.0	1.2	

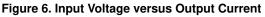
#### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)



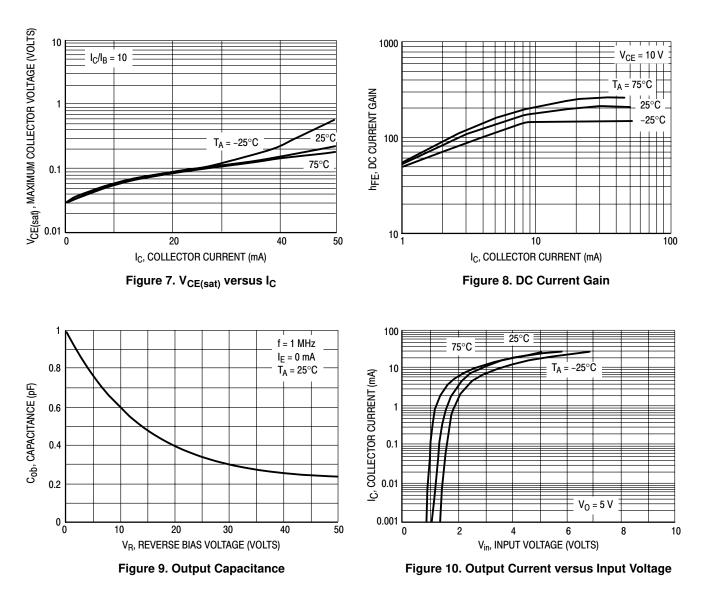
### **TYPICAL ELECTRICAL CHARACTERISTICS – PNP TRANSISTOR**







## TYPICAL ELECTRICAL CHARACTERISTICS - NPN TRANSISTOR



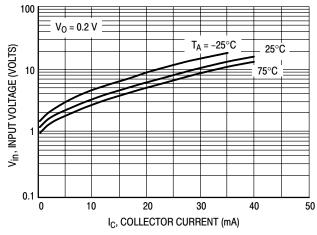
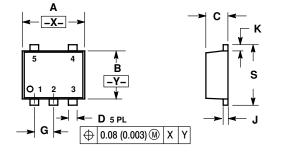


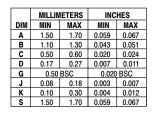
Figure 11. Input Voltage versus Output Current

### PACKAGE DIMENSIONS

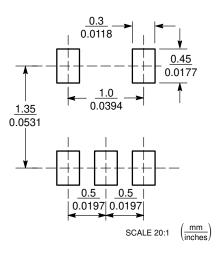
SOT-553 **XV5 SUFFIX** 5-LEAD PACKAGE CASE 463B-01 **ISSUE A** 

NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETERS 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL MATERIAL.





#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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